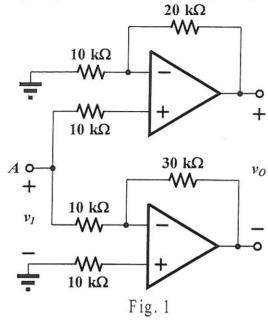
國立臺灣師範大學 104 學年度碩士班招生考試試題

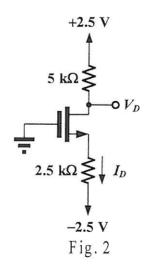
科目:電子學 適用系所:電機工程學系

注意:1.本試題共 3 頁,請依序在答案卷上作答,並標明題號,不必抄題。2.答案必須寫在指定作答區內,否則不予計分。

1. (10 points) The circuit shown in Fig. 1 is intended to supply a voltage to floating loads. Assuming ideal op amps, find the voltage gain v_O/v_I .



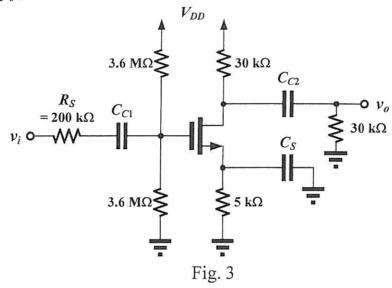
- 2. (20 points) The NMOS transistor in the circuit of Fig. 2 has $\mu_n C_{ox} = 100 \ \mu\text{A/V}^2$, $W = 32 \ \mu\text{m}$, $L = 1 \ \mu\text{m}$, and $V_t = 1 \ \text{V}$. Neglect the channel-length modulation effect (i.e., assume $\lambda = 0$). Find
 - (a) the overdrive voltage V_{OV} .
 - (b) the drain current I_D .
 - (c) the drain voltage V_D .



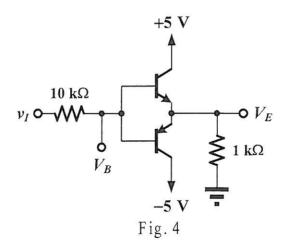
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- 3. (15 points) For the CS amplifier shown in Fig. 3, a signal source v_i with an internal resistance $R_S = 200 \text{ k}\Omega$. The NMOS transistor is operated in saturation region and has $r_o = 150 \text{ k}\Omega$, $g_m = 0.2 \text{ mA/V}$, $C_{gs} = 1 \text{ pF}$, and $C_{gd} = 0.5 \text{ pF}$. Find
 - (a) the midband gain $A_M \equiv v_o/v_i$.
 - (b) the upper 3-dB frequency f_H .
 - (c) the appropriate value of the bypass capacitor C_S to have the lower 3-dB frequency f_L at 100 Hz.

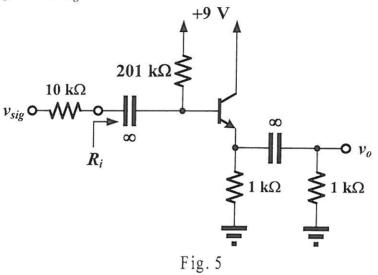


- 4. (20 points) For the circuit of Fig. 4, the BJTs have $\beta = 100$, $|V_{BE}| = 0.7$ V, and $|V_{CEsat}| = 0.2$ V. Find V_B and V_E for
 - (a) $v_I = 3 \text{ V}$.
 - (b) $v_I = -10 \text{ V}.$



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- 5. (20 points) For the emitter-follower circuit shown in Fig. 5, the BJT used is specified to have $\beta = 200$, $V_{BE(active)} = 0.7$ V, and $V_T = 25$ mV. Find
 - (a) I_E , V_E , and V_B .
 - (b) the input resistance R_i .
 - (c) the signal gain v_o/v_{sig} .



6. (15 points) The voltage-to-current converter, as shown in Fig. 6, can supply the load impedance Z_L with a current i_O proportional to v_I and independent of the value of Z_L . Show that this is indeed the case by deriving the output current i_O as a function of v_I .

